NSN 5962-01-325-0481

Memory Microcircuit - Page 1 of 2

View Online at https://aerobasegroup.com/nsn/5962-01-325-0481

Overall Length:

1.290 inches

Overall Height:

0.425 inches

Overall Width:

0.620 inches

Body Length:

1.290 inches

Body Width:

0.610 inches

Body Height:

0.210 inches

Maximum Power Dissipation Rating:

950.0 milliwatts

Operating Tempurature Range:

-55.0/+125.0 degrees celsius

Storage Tempurature Range:

-65.0/+150.0 degrees celsius

Features Provided:

Bipolar and burn in and monolithic and electrostatic sensitive and programmable and schottky

Inclosure Material:

Ceramic

Inclosure Configuration:

Dual-in-line

Output Logic Form:

Complementary-metal oxide-semiconductor logic

Input Circuit Pattern:

16 input

Case Outline Source And Designator:

D-3 mil-m-38510

Terminal Surface Treatment:

Solder

Voltage Rating And Type Per Characteristic:

-0.5 volts power source and 7.0 volts power source

Time Rating Per Chacteristic:

90.00 nanoseconds propagation delay time, low to high level output and 90.00 nanoseconds propagation delay time, high to low level output

Memory Device Type:

Rom

Test Data Document:

96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).

Terminal Type And Quantity:

24 printed circuit

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

Yes - demil/mli

Fiig:

A458a0